ABSTRACT OF THE DISCLOSURE

ORGANOSILICON PRECURSORS FOR INTERLAYER DIELECTRIC FILMS WITH LOW DIELECTRIC CONSTANTS

A method of forming a low dielectric constant interlayer dielectric film on a substrate by reacting, under chemical vapor deposition conditions sufficient to deposit the film on the substrate, an organosilicon precursor comprising a silyl ether, a silyl ether oligomer, or an organosilicon compound containing one or more reactive groups, to form an interlayer dielectric film having a dielectric constant of 3.5 or less. The films formed by the above method.

Figure 1